

ABSTRACT OF THE DISCLOSURE

A high potential barrier is prevented from being formed on a hetero-boundary surface between a p-type AlGaInP cladding layer and a p-type GaP window layer by forming an insertion layer having a smaller band gap energy than that of the p-type AlGaInP cladding layer therebetween. The insertion layer serves as a forward voltage reducing layer, and the forward voltage of a LED is lowered.

(Selected drawing is Fig. 3)